

# EAST Search History (z1 pp.1) ~~48~~

| Ref # | Hits   | Search Query   | DBs   | Default Operator | Plurals | Time Stamp       |
|-------|--------|--|---|------------------|---------|------------------|
| L1    | 1858   | 257/77   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2006/09/26 13:40 |
| L2    | 251    | 257/78   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2006/09/26 13:40 |
| L3    | 12     | /183   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2006/09/26 13:40 |
| L4    | 215956 | "197"  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2006/09/26 13:40 |
| L5    | 375853 | "198"  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2006/09/26 13:40 |
| L6    | 3413   | ((257/77) or (257/78) or<br>(257/183) or (257/197) or<br>(257/198) or (438/931)).CCLS.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | OFF     | 2006/09/26 14:16 |
| L7    | 1      | 6 and (single adj ((crystal<br>crystalline crystallinity monocrystal<br>monocrystalline monocrystallinity<br>mono-crystal mono-crystalline<br>mono-crystallinity) near4 (si<br>silicon))) and (single adj ((crystal<br>crystalline crystallinity monocrystal<br>monocrystalline monocrystallinity<br>mono-crystal mono-crystalline<br>mono-crystallinity))) near4 (sic<br>silicon adj carbide) and (abrupt<br>abruptly steep steeply slope<br>sloping graded grading sloped<br>drastic sudden drastically<br>suddenly) and (oxygen "O. <sub>2</sub> "<br>O) near8 (density concentration<br>abundance) near8 (silicon adj<br>carbide silicon si sic) and<br>(thickness thick) near4 (layer film) | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/09/26 14:17 |

## EAST Search History

|     |      |   |   |    |     |                  |
|-----|------|---|---|----|-----|------------------|
| L9  | 1    | 7 and (c carbon) near1 concentration  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/09/26 14:11 |
| L10 | 3778 | ((257/77) or (257/78) or (257/183) or (257/197) or (257/198) or (257/616) or (438/931)).CCLS.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/09/26 14:17 |
| L11 | 1    | 10 and (single adj ((crystal crystalline crystallinity monocrystal monocystalline monocrystallinity mono-crystal mono-crystalline mono-crystallinity) near4 (si silicon))) and (single adj ((crystal crystalline crystallinity monocrystal monocystalline monocrystallinity mono-crystal mono-crystalline mono-crystallinity)) near4 (sic silicon adj carbide) and (abrupt abruptly steep steeply slope sloping graded grading sloped drastic sudden drastically suddenly) and (oxygen "O. <sub>2</sub> " O) near8 (density concentration abundance) near8 (silicon adj carbide silicon si sic) and (thickness thick) near4 (layer film)                | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/09/26 14:26 |
| L12 | 1    | 10 and (single adj ((crystal crystalline crystallinity monocrystal monocystalline monocrystallinity mono-crystal mono-crystalline mono-crystallinity) near4 (si silicon))) and (single adj ((crystal crystalline crystallinity monocrystal monocystalline monocrystallinity mono-crystal mono-crystalline mono-crystallinity)) near4 (sic silicon adj carbide) and (abrupt abruptly steep steeply slope sloping graded grading sloped drastic sudden drastically suddenly) and (oxygen "O. <sub>2</sub> " O) near8 (density concentration abundance) near8 (silicon adj carbide silicon si sic) and (thickness thick) near4 (layer film) and transistor | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/09/26 14:27 |

## EAST Search History

|     |      |   |   |    |     |                  |
|-----|------|---|---|----|-----|------------------|
| L14 | 488  | uhv-cvd   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/09/26 14:43 |
| L15 | 1874 | uhv-cvd.ti,ab,clm. (ultra adj high adj vacuum).ti,ab,clm.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/09/26 14:43 |
| L16 | 156  | uhv-cvd.ti,ab,clm. ((ultra adj high adj vacuum).ti,ab,clm. and cvd.ti, ab,clm.)   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/09/26 14:44 |
| L17 | 89   | uhv-cvd.ti,ab,clm. ((ultra adj high adj vacuum).ti,ab,clm. and cvd.ti, ab,clm.) and silicon adj carbide   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/09/26 14:45 |
| L27 | 532  | (257/198).CCLS.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/09/26 15:01 |
| L28 | 71   | 27 and (sic silicon adj carbide)  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/09/26 15:12 |
| L29 | 29   | 27 and (sic silicon adj carbide) and (uhv-cvd oxygen O)   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/09/26 15:19 |
| L30 | 24   | 27 and (sic silicon adj carbide) and (uhv-cvd oxygen O) and (profile density graded grading abrupt steep sharp)                                       | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/09/26 15:28 |
| L31 | 0    | 27 and (sic silicon adj carbide) and (uhv-cvd or ((carbon c) near4 profile concentration density)) and oxygen near4 (concentration density abundance) | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/09/26 15:35 |
| L32 | 3541 | ((257/77) or (257/197) or (257/198) or (257/616) or (257/183) or (438/931)).CCLS.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/09/26 16:16 |

## EAST Search History

|     |     |   |   |    |     |                  |
|-----|-----|---|---|----|-----|------------------|
| L33 | 7   | 32 and (sic silicon adj carbide) and (silicon si) and ((uhv-cvd ultra adj high adj vacuum ultra-high-vacuum) near4 (cvd chamical adj vapo\$1or adj deposition) or ((abrupt steep\$2 sharp\$2) near4 (profile gradient graded increas\$3 decreas\$3))) and ("O" "O.sub."\$1 oxygen) near3 (content concentration density)                    | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2006/09/26 16:16 |
| L34 | 1   | 32 and (sic silicon adj carbide) and (silicon si) and ((uhv-cvd ultra adj high adj vacuum ultra-high-vacuum) near4 (cvd chamical adj vapo\$1or adj deposition) or ((abrupt steep\$2 sharp\$2) near4 (profile gradient graded increas\$3 decreas\$3))) and ("O" "O.sub."\$1 oxygen) near3 (content concentration density) and @ad<"20010421" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2006/09/26 15:54 |
| L35 | 1   | (silicon adj carbide sic).clm. and ((mono single) adj (crystal crystalline) (monocrystal monocrystalline) (mono-crystal mono-crystalline single-crystal single-crystalline)).clm. and ((c carbon) near4 (concentration density abundance)).clm. and (oxygen "O") near4 ("10.sup."\$3). clm.   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2006/09/26 16:16 |
| L36 | 0   | (silicon adj carbide sic).clm. and ((mono single) adj (crystal crystalline) (monocrystal monocrystalline) (mono-crystal mono-crystalline single-crystal single-crystalline)).clm. and ((c carbon) near4 (concentration density abundance)).clm. and (oxygen "O") near4 ("10.sup."\$3). clm. and @ad<"20010421"                              | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2006/09/26 16:15 |
| L37 | 728 | ((257/613) or (257/616)).CCLS.  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/09/26 16:15 |

## EAST Search History

|     |      |  |   |    |     |                  |
|-----|------|--|---|----|-----|------------------|
| L38 | 0    | 37 and (silicon adj carbide sic).<br>clm. and ((mono single) adj<br>(crystal crystalline) (monocrystal<br>monocrystalline) (mono-crystal<br>mono-crystalline single-crystal<br>single-crystalline)).clm. and ((c<br>carbon) near4 (concentration<br>density abundance)).clm. and<br>(oxygen "O") near4 ("10.sup."\$3).<br>clm.                         | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/09/26 16:16 |
| L39 | 3794 | ((257/77) or (257/197) or<br>(257/198) or (257/613) or<br>(257/616) or (257/183) or<br>(438/931)).CCLS.  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/09/26 16:16 |
| L40 | 7    | 39 and (sic silicon adj carbide) and<br>(silicon si) and ((uhv-cvd ultra adj<br>high adj vacuum<br>ultra-high-vacuum) near4 (cvd<br>chamical adj vapo\$1or adj<br>deposition) or ((abrupt steep\$2<br>sharp\$2) near4 (profile gradient<br>graded increas\$3 decreas\$3)))<br>and ("O" "O.sub."\$1 oxygen)<br>near3 (content concentration<br>density) | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/09/26 16:21 |
| L41 | 19   | (("5780327") or ("5906951") or<br>("6723621") or ("6013134") or<br>("6096590") or ("6350993") or<br>("6251751") or ("6059895") or<br>("6425951") or ("6475072")).PN.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/09/26 16:26 |
| L42 | 0    | ("jagganathan.in.").PN.  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/09/26 16:27 |
| L43 | 0    | ("jagannathan.in.").PN.  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/09/26 16:27 |
| L44 | 544  | jagannathan.in.  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/09/26 16:27 |
| L45 | 38   | (basanth near2 jagannathan).in.  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/09/26 16:28 |

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|     |    |   |   |    |     |                  |
|-----|----|---|---|----|-----|------------------|
| L46 | 38 | (basanth near2 jagannathan).in.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/09/26 16:39 |
| L47 | 0  | ("711640.ap.753001.ap.908448.ap.").PN.  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/09/26 16:39 |
| L48 | 17 | "711640".ap. "753001".ap.<br>"908448".ap.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/09/26 16:49 |
| L49 | 2  | ("5777364").PN.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/09/26 16:53 |
| L50 | 2  | ("5352912").PN.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/09/26 16:53 |
| S1  | 4  | "775514".ap.  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/04/16 14:02 |
| S2  | 6  | (("6,285,064") or ("6,358,773") or<br>("6,368,888")).PN.  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/04/03 22:06 |
| S3  | 1  | (US-20040161875-\$).did.  | US-PGPUB  | OR | OFF | 2005/04/03 22:08 |
| S4  | 10 | (silicon adj carbide sic) near20<br>graded near20 buffer and single<br>adj (crystalline crystal) near4<br>(silicon si)  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/04/03 22:13 |
| S5  | 2  | (silicon adj carbide sic) near20<br>graded near20 buffer and single<br>adj (crystalline crystal) near4<br>(silicon si) and (thick thickness)<br>near10 buffer | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/04/03 22:18 |

## EAST Search History

|     |     |   |   |    |     |                  |
|-----|-----|---|---|----|-----|------------------|
| S6  | 2   | ("6750119").PN.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/04/03 22:18 |
| S7  | 1   | "5683934".PN.   | USPAT;<br>USOCR   | OR | OFF | 2005/04/03 22:19 |
| S8  | 1   | "5906680".PN.   | USPAT;<br>USOCR   | OR | OFF | 2005/04/03 22:19 |
| S9  | 1   | "6190975".PN.   | USPAT;<br>USOCR   | OR | OFF | 2005/04/03 22:20 |
| S10 | 1   | "20020160605".PN.   | US-PGPUB  | OR | OFF | 2005/04/03 22:20 |
| S11 | 155 | junction near4 (sic silicon adj carbide) near4 (si silicon) and (monocrystalline single adj (crystal crystalline))  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/04/04 09:50 |
| S12 | 15  | (US-20010015170-\$).did. or (US-6472594-\$ or US-6273950-\$ or US-6214107-\$ or US-6183857-\$ or US-5861324-\$ or US-5847418-\$ or US-5726440-\$ or US-5681402-\$ or US-5671914-\$ or US-5599403-\$ or US-5459089-\$ or US-5456762-\$ or US-5449923-\$).did. or (JP-62216364-\$).did. | US-PGPUB;<br>USPAT;<br>JPO                              | OR | OFF | 2005/04/04 09:49 |
| S13 | 144 | S11 and (interface thick thickness abrupt sharp buffer)   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/04/04 09:51 |
| S14 | 14  | S12 and (interface thick thickness abrupt sharp buffer)   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/04/04 09:51 |
| S15 | 7   | S12 and (interface thick thickness abrupt sharp buffer) and ("SiC/Si" "Si/SiC")   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/04/04 10:13 |
| S16 | 3   | (("5298452") or ("5906680")).PN.  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/04/04 10:01 |

## EAST Search History

|     |      |   |   |    |     |                  |
|-----|------|---|---|----|-----|------------------|
| S17 | 0    | (257/77 and uhf-cvd and ("S/SiC""SiC/S")).CCLS.                     | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/04 10:02 |
| S18 | 0    | 257/77 and uhf-cvd and ("S/SiC""SiC/S")                             | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/04 10:02 |
| S19 | 0    | 257/77 and uhf-cvd and ("S/SiC""SiC/S")                             | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2005/04/04 10:02 |
| S20 | 0    | 257/77 and uhf near1 cvd  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2005/04/04 10:03 |
| S21 | 0    | 257/77 and uhf adj cvd  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2005/04/04 10:03 |
| S22 | 0    | 257/77.ccls. and uhf adj cvd  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2005/04/04 10:03 |
| S23 | 3    | 257/77.ccls. and uhf and cvd  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2005/04/04 10:03 |
| S24 | 1260 | ((257/77) or (438/931)).CCLS.                                       | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/29 07:26 |
| S25 | 47   | S24 and ("Si/SiC" "SiC/S" interface junction) near10 (abrupt sharp) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2005/04/04 10:24 |
| S26 | 5    | S24 and hbt and buffer and graded and (thick thickness thin)        | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2005/04/04 11:40 |

## EAST Search History

|     |     |   |   |    |     |                  |
|-----|-----|---|---|----|-----|------------------|
| S27 | 0   | (single adj (crystalline crystal) monocrystalline) near3 (silicon "Si") near6 (silicon adj carbide "SiC") and graded near4 ("Si.sub. "\$3"C.sub."\$3)   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2005/04/04 11:44 |
| S28 | 363 | (single adj (crystalline crystal) monocrystalline) near1 (silicon "Si") near2 substrate near6 (silicon adj carbide "SiC")   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2005/04/04 11:45 |
| S29 | 0   | (single adj (crystalline crystal) monocrystalline) near1 (silicon "Si") near2 substrate near6 (silicon adj carbide "SiC") and (buffer graded) near4 ("Si.sub.xC.sub.1-x" "Si.sub.1-xC.sub.x") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2005/04/04 11:46 |
| S30 | 0   | (single adj (crystalline crystal) monocrystalline) near1 (silicon "Si") near2 substrate near6 (silicon adj carbide "SiC") and "Si.sub. "\$3"C.sub."\$3  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2005/04/04 11:47 |
| S31 | 363 | (single adj (crystalline crystal) monocrystalline) near1 (silicon "Si") near2 substrate near6 (silicon adj carbide "SiC")   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2005/04/04 11:48 |
| S32 | 179 | (single adj (crystalline crystal) monocrystalline) near1 (silicon "Si") near2 substrate near6 (silicon adj carbide "SiC") not (silicon adj carbide adj substrate)                             | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2005/04/04 12:19 |
| S33 | 10  | (("5,906,680") or ("6,190,975") or ("20010160605") or ("5,683,934") or ("20020016085") or ("6,306, 211")).PN.   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/04 12:24 |
| S34 | 10  | (("5,906,680") or ("6,190,975") or ("5,683,934") or ("20020016085") or ("6,306,211")).PN. or (2001/0160605).CCLS.   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/04 12:24 |
| S35 | 0   | ("20010160605").PN.   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/04 12:25 |

## EAST Search History

|     |     |  |   |    |     |                  |
|-----|-----|--|---|----|-----|------------------|
| S36 | 0   | (2001/0160605).CCLS.                   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/04/04 12:25 |
| S37 | 85  | kanazawa.in. and "200210"\$2.pd.       | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/04/04 12:26 |
| S38 | 273 | kanazawa.in. and silicon               | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/04/04 12:26 |
| S39 | 31  | kanazawa.in. and silicon               | US-PGPUB  | OR | OFF | 2005/04/04 12:31 |
| S40 | 26  | kanazawa.in. and silicon and substrate | US-PGPUB  | OR | OFF | 2005/04/04 12:26 |
| S41 | 0   | @pd="200210"\$2 and kanazawa.in.       | US-PGPUB  | OR | OFF | 2005/04/04 12:31 |
| S42 | 202 | kanazawa.in.                           | US-PGPUB  | OR | OFF | 2005/04/04 12:32 |
| S43 | 4   | suemitsu.in. and sic adj film          | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/04/04 12:53 |
| S44 | 0   | suemitsu.in. and nakazaka.in.          | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/04/04 12:53 |
| S45 | 4   | suemitsu.in. and nakazawa.in.          | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/04/04 12:59 |
| S46 | 0   | ("20010160605").PN.                    | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/04/04 12:58 |
| S47 | 2   | ("2001160605").PN.                     | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/04/04 12:58 |

## EAST Search History

|     |       |   |   |    |     |                  |
|-----|-------|---|---|----|-----|------------------|
| S48 | 15481 | nakazawa.in.  | US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB           | OR | OFF | 2005/04/04 12:59 |
| S49 | 125   | nakazawa.in. and "200210"\$2.pd.  | US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB           | OR | OFF | 2005/04/04 13:01 |
| S50 | 187   | nakazawa.in. and substrate  | US-PGPUB  | OR | OFF | 2005/04/04 13:57 |
| S51 | 0     | (2004/0161875).CCLS.  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/04/04 13:57 |
| S52 | 2     | ("20040161875").PN.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/04/04 13:58 |
| S53 | 2     | ("200?0161875").PN.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/04/04 13:58 |
| S54 | 0     | ("20010160605").PN.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/04/04 13:59 |
| S55 | 0     | ("(monocrystallinesingleadjcrystal)<br>near2(siliconSi)and(carbonC)and(c<br>oncentrationprofile)").PN.  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/04/27 10:25 |
| S56 | 8580  | (monocrystalline single adj crystal)<br>near2 (silicon Si) and (carbon C)<br>and (concentration profile) and<br>boron                           | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/04/27 10:26 |
| S57 | 1322  | (monocrystalline single adj crystal)<br>near2 (silicon Si) and (carbon C)<br>and (concentration profile) and<br>boron near5 (barrier diffusion) | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/04/27 10:26 |

## EAST Search History

|     |     |  |   |    |     |                  |
|-----|-----|--|---|----|-----|------------------|
| S58 | 85  | (monocrystalline single adj crystal) near2 (silicon Si) and (carbon C) and (concentration profile) and boron near5 (barrier diffusion) and (hbt heterojunction adj bipolar adj transistor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2005/04/27 10:27 |
| S59 | 456 | gated adj diode  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/04/27 12:14 |
| S60 | 73  | gated adj diode.ti.  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2005/04/27 12:15 |
| S61 | 3   | "751714".ap.   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2005/04/27 12:16 |
| S62 | 46  | boron near1 diffusion and (silicon adj carbide SiC) and concentration near3 profile and (silicon Si) near3 substrate   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2005/04/28 08:55 |
| S63 | 0   | intrinsic adj buffer near3 (silicon si) near6 (crystalline monocrystalline single adj crystal) and hbt   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2005/04/28 08:57 |
| S64 | 188 | buffer near3 (silicon si) near6 (crystalline monocrystalline single adj crystal) and hbt   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2005/04/28 09:23 |
| S65 | 0   | collector near4 lattice and S64  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2005/04/28 09:23 |
| S66 | 0   | collector near10 lattice and S64   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2005/04/28 09:23 |

## EAST Search History

|     |    |  |   |    |     |                  |
|-----|----|--|---|----|-----|------------------|
| S67 | 8  | collector near10 lattice and S62   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/04/28 10:23 |
| S68 | 27 | (single adj crystalline monocrystalline) near2 emitter and hbt   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/04/28 10:32 |
| S69 | 1  | (single adj crystalline monocrystalline) near2 emitter near5 (mobility conductivity resistivity) and hbt | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/04/28 11:05 |
| S70 | 13 | (single adj crystalline monocrystalline) near2 emitter near5 (mobility conductivity resistivity)         | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/04/28 11:05 |
| S71 | 88 | polycrystalline near3 emitter and hbt  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/04/28 12:44 |
| S72 | 27 | polycrystalline near3 emitter and hbt and (carbide SiC)  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/04/28 12:45 |
| S73 | 1  | polycrystalline near3 (carbide SiC) near4 emitter and hbt and (carbide SiC)                              | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/04/28 12:46 |
| S74 | 1  | polycrystalline near3 (carbide SiC) near4 emitter and hbt  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2005/04/28 12:46 |
| S75 | 2  | ("6137120").PN.  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/04/28 13:09 |
| S76 | 95 | fang.in. and emitter   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/04/28 13:10 |

## EAST Search History

|     |    |  |   |    |     |                  |
|-----|----|--|---|----|-----|------------------|
| S77 | 5  | (("5,906,680") or ("6,190,975") or ("20010160605") or ("5,683,934") or ("20020016085") or ("6,306,211")).PN.   | US-PGPUB;<br>USPAT                                      | OR | OFF | 2005/04/29 07:11 |
| S78 | 59 | (US-20010015170-\$ or US-20020016085-\$ or US-20020094658-\$ or US-20020102862-\$ or US-20020124793-\$ or US-20020158311-\$ or US-20020158313-\$ or US-20020160605-\$ or US-20020182423-\$ or US-20020192918-\$ or US-20030054601-\$ or US-20040089918-\$ or US-20040161875-\$ or US-20040195655-\$ or US-20040198010-\$ or US-20040217430-\$ or US-20050006663-\$ or US-20050023642-\$ or US-20050051798-\$ or US-20050064645-\$ or US-20050082571-\$).did. or (US-5296258-\$ or US-5298452-\$ or US-5449923-\$ or US-5456762-\$ or US-5459089-\$ or US-5599403-\$ or US-5670414-\$ or US-5671914-\$ or US-5681402-\$ or US-5683934-\$ or US-5726440-\$ or US-5847418-\$ or US-5861324-\$ or US-5906680-\$ or US-6064081-\$ or US-6183857-\$ or US-6190975-\$ or US-6214107-\$ or US-6273950-\$ or US-6285064-\$ or US-6306211-\$ or US-6358773-\$ or US-6362065-\$ or US-6368888-\$ or US-6472594-\$ or US-6552375-\$).did. or (US-6673662-\$ or US-6750119-\$).did. or (JP-62216364-\$).did. or (DE-3777507-\$ or EP-703628-\$ or EP-829908-\$ or EP-908984-\$ or EP-1039512-\$ or US-20020016085-\$ or US-6285064-\$ or US-6358773-\$ or US-20020102862-\$).did. | US-PGPUB;<br>USPAT;<br>JPO;<br>DERWENT                  | OR | OFF | 2005/04/29 07:14 |
| S79 | 0  | ("2andkanazawa.in.").PN.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/04/29 07:14 |

## EAST Search History

|     |      |  |   |    |     |                  |
|-----|------|--|---|----|-----|------------------|
| S80 | 0    | S78 and kanazawa.in.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/04/29 07:15 |
| S81 | 2    | S78 and nakazawa.in.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/04/29 07:15 |
| S82 | 2120 | ((257/77) or (257/183) or (257/197) or (257/198) or (438/931)).CCLS.             | US-PGPUB;<br>USPAT                                      | OR | OFF | 2005/04/29 08:04 |
| S83 | 355  | S82 and silicon adj carbide and boron  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/04/29 07:31 |
| S84 | 10   | S82 and silicon adj carbide and boron and (uhv ultra adj "high" adj vacuum)      | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/04/29 08:05 |
| S85 | 2300 | ((257/77) or (257/78) or (257/183) or (257/197) or (257/198) or (438/931)).CCLS. | US-PGPUB;<br>USPAT                                      | OR | OFF | 2005/04/29 08:04 |
| S86 | 180  | S85 NOT S82  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/04/29 08:05 |
| S87 | 0    | S86 and silicon adj carbide and boron and (uhv ultra adj "high" adj vacuum)      | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/04/29 08:05 |
| S88 | 4    | "775514".ap.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/09/24 16:36 |
| S89 | 2    | ("6552375").PN.  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/09/24 16:54 |

## EAST Search History

|     |      |  |   |    |     |                  |
|-----|------|--|---|----|-----|------------------|
| S90 | 0    | laser adj melting near4 sic  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/09/24 16:54 |
| S91 | 222  | mbe near4 sic  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/09/24 17:00 |
| S92 | 121  | lattice adj constant near4 sic   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/09/24 17:00 |
| S93 | 35   | lattice adj constant near1 sic   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/09/24 17:15 |
| S94 | 3    | laser adj melting.ti. and (sic silicon<br>adj carbide silicon adj germanium<br>sig)  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/09/24 17:32 |
| S95 | 12   | (("5906680") or ("6190975") or<br>("5693934") or ("6306211") or<br>("20020160605") or<br>("20020016085")).PN.  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/09/24 17:33 |
| S96 | 12   | (("5906680") or ("6190975") or<br>("5683934") or ("6306211") or<br>("20020160605") or<br>("20020016085")).PN.  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/09/24 19:50 |
| S97 | 2418 | ((257/77) or (257/78) or<br>(257/183) or (257/197) or<br>(257/198) or (438/931)).CCLS.   | US-PGPUB;<br>USPAT                                      | OR | OFF | 2005/09/24 19:50 |
| S98 | 1    | S97 and (single adj crystalline<br>monocrystal monocrystalline)<br>near4 (Si silicon).ti,ab,clm. and<br>(silicon adj carbide Sic).ti,ab,clm.<br>and oxygen near4 (concentration<br>content density).ti,ab,clm. and<br>interface.ti,ab,clm. | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2005/09/24 20:02 |

## EAST Search History

|       |     |  |   |    |     |                  |
|-------|-----|--|---|----|-----|------------------|
| S99   | 4   | (single adj crystalline monocrystal monocrystalline) near4 (Si silicon).ti,ab,clm. and (silicon adj carbide Sic).ti,ab,clm. and oxygen near4 (concentration content density).ti,ab,clm. and interface.ti,ab,clm.                                       | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/09/24 20:09 |
| S10 0 | 226 | (single adj crystalline monocrystal monocrystalline) near4 (Si silicon) and (silicon adj carbide Sic) and oxygen near4 (concentration content density) and interface   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2005/09/24 20:10 |
| S10 1 | 4   | (single adj crystalline monocrystal monocrystalline) near4 (Si silicon).ti,ab,clm. and (silicon adj carbide Sic).ti,ab,clm. and oxygen near4 (concentration content density).ti,ab,clm. and interface.ti,ab,clm.                                       | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2005/09/24 20:09 |
| S10 2 | 190 | (single adj crystalline monocrystal monocrystalline) near4 (Si silicon) and (silicon adj carbide Sic) and oxygen near2 (concentration content density) and interface   | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2005/09/24 20:25 |
| S10 3 | 2   | ("5929259").PN.  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/09/24 20:19 |
| S10 4 | 60  | (single adj crystalline monocrystal monocrystalline) near4 (Si silicon) and (silicon adj carbide Sic) and oxygen near2 (concentration content density) and interface and (dopant doping) near2 (concentration density)                                 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2005/09/24 20:29 |
| S10 5 | 3   | (single adj crystalline monocrystal monocrystalline) near4 (Si silicon) and (silicon adj carbide Sic) and oxygen near2 (concentration content density) and interface and (dopant doping) near2 (concentration density) near6 (silicon adj carbide sic) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON  | 2005/09/24 20:29 |
| S10 6 | 0   | "5298254".pn. and UHV-CVD  | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2006/04/16 14:06 |

## EAST Search History

|          |    |   |   |    |     |                  |
|----------|----|---|---|----|-----|------------------|
| S10<br>7 | 2  | "5298254".pn.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/04/16 14:07 |
| S10<br>8 | 2  | "5298452".pn.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/04/16 14:26 |
| S10<br>9 | 0  | S108 and (single adj crystal single<br>adj crystalline monocrystal<br>monocrystalline) near4 (SiC silicon<br>adj carbide) | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/04/16 14:27 |
| S11<br>0 | 0  | S108 and (SiC silicon adj carbide)  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/04/16 14:27 |
| S11<br>1 | 1  | (US-20040161875-\$).did.  | US-PGPUB  | OR | OFF | 2006/04/16 14:28 |
| S11<br>3 | 2  | "6552375".pn.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/04/16 14:48 |
| S11<br>4 | 0  | S113 and (SiC silicon adj carbide)<br>near4 (single monocrystal<br>monocrystalline)                                       | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/04/16 14:40 |
| S11<br>5 | 26 | vpe near4 (single adj crystal\$4)   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/04/16 14:48 |
| S11<br>6 | 7  | vpe near4 (single adj crystal\$4)<br>near4 sic  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/04/16 14:56 |
| S11<br>7 | 26 | vpe near4 (single adj crystal\$4)"ti,<br>ab,clm."   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/04/16 14:56 |

## EAST Search History

|          |      |  |   |    |     |                  |
|----------|------|--|---|----|-----|------------------|
| S11<br>8 | 7    | vpe near4 (single adj crystal\$4).ti,<br>ab,clm.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/04/16 16:02 |
| S11<br>9 | 2316 | shibahara.in.  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/04/16 16:02 |
| S12<br>0 | 0    | shibahára.in. and step-controlled  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/04/16 16:02 |
| S12<br>1 | 7    | shibahara.in. and sic  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/04/16 16:14 |
| S12<br>2 | 0    | vpe near4 single adj crystal near4<br>sic  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/04/16 16:14 |
| S12<br>3 | 7    | vpe near4 (single adj crystal\$3)<br>near4 sic   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/04/16 16:41 |
| S12<br>4 | 25   | (diffusion adj barrier) near4<br>(single adj crystal\$4)   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/04/16 17:22 |
| S12<br>5 | 3294 | ((257/77) or (257/78) or<br>(257/183) or (257/197) or<br>(257/198) or (438/931)).CCLS.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/04/16 17:22 |
| S12<br>6 | 1    | S125 and abrupt near2 (junction<br>interface).ti,ab,clm. and carbon<br>near2 (density concentration ratio<br>abundance).ti,ab,clm. and<br>(monocrystal single adj crystal<br>crystalline monocrystalline mon<br>adj crystalline) near4 (silicon adj<br>carbide SiC).ti,ab,clm. | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/04/16 17:25 |

## EAST Search History

|          |       |  |   |    |     |                  |
|----------|-------|--|---|----|-----|------------------|
| S12<br>7 | 3     | "6552375"  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/09/21 09:22 |
| S12<br>8 | 8     | "144786".ap.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/09/21 10:46 |
| S12<br>9 | 0     | (uhf-cvd (uhf adj cvd) ultra adj "high" adj frequency) near3 (cvd chemical adj vapo\$1r adj deposition) and (silicon si) and (silicon adj carbide sic) | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/09/21 10:49 |
| S13<br>0 | 3     | (uhf-cvd (uhf adj cvd) ultra adj "high" adj frequency) near3 (cvd chemical adj vapo\$1r adj deposition)  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/09/21 10:55 |
| S13<br>1 | 3     | (uhf-cvd (uhf adj cvd)) ((ultra adj "high" adj frequency) near3 (cvd chemical adj vapo\$1r adj deposition))  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/09/21 10:57 |
| S13<br>2 | 13577 | (uhf-cvd (uhf adj cvd)) (ecr (ultra adj "high" adj frequency) near3 (cvd chemical adj vapo\$1r adj deposition))  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/09/21 10:57 |
| S13<br>3 | 33    | (uhf-cvd uhf-ecr (uhf adj cvd)) ((ultra adj "high" adj frequency) near3 (cvd chemical adj vapo\$1r adj deposition))                                    | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/09/21 10:59 |
| S13<br>4 | 4     | (uhf-cvd (uhf adj cvd)) (((ultra adj "high" adj frequency) uhf) near3 (cvd chemical adj vapo\$1r adj deposition))                                      | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/09/21 11:02 |
| S13<br>5 | 6     | oxygen adj (concenteration impurity) near6 (sic silicon adj carbide)   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/09/21 11:03 |
| S13<br>6 | 40    | oxygen adj (concentration impurity) near6 (sic silicon adj carbide)  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/09/21 11:06 |

## EAST Search History

|          |     |  |   |    |     |                  |
|----------|-----|--|---|----|-----|------------------|
| S13<br>7 | 2   | ("6750119").PN.  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | OFF | 2006/09/21 11:12 |
| S13<br>8 | 835 | diffusion adj (constant rate coefficient) near3 (carbon C)                       | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/09/21 11:13 |
| S13<br>9 | 62  | diffusion adj (constant rate coefficient) near4 (carbon C)<br>near4 (silicon Si) | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/09/21 13:19 |
| S14<br>0 | 3   | "6906680".pn.  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/09/21 13:19 |
| S14<br>1 | 2   | "5906680".pn.  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/09/21 13:59 |
| S14<br>2 | 1   | "5906680".pn. and abrupt   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/09/21 14:00 |
| S14<br>3 | 1   | "5906680".pn. and abrupt and thick\$4  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON  | 2006/09/21 16:33 |

*inv. name search. (15 pp.)*

Day : Tuesday  
Date: 9/26/2006  
Time: 16:38:11

# PALM INTRANET

## Inventor Name Search Result

Your Search was:

Last Name = JAGANNATHAN

First Name = BASANTH

| Application#                    | Patent#                        | Status | Date Filed | Title  | Inventor Name           |
|---------------------------------|--------------------------------|--------|------------|--|-------------------------|
| <a href="#"><u>09633857</u></a> | <a href="#"><u>6881259</u></a> | 150    | 08/07/2000 | IN-SITU MONITORING AND CONTROL OF GERMANIUM PROFILE IN SILICON-GERMANIUM ALLOY FILMS AND TEMPERATURE MONITORING DURING DEPOSITION OF SILICON FILMS | JAGANNATHAN,<br>BASANTH |
| <a href="#"><u>09683088</u></a> | <a href="#"><u>6875279</u></a> | 150    | 11/16/2001 | SINGLE REACTOR, MULTI-PRESSURE CHEMICAL VAPOR DEPOSITION FOR SEMICONDUCTOR DEVICES   | JAGANNATHAN,<br>BASANTH |
| <a href="#"><u>09683983</u></a> | <a href="#"><u>6744079</u></a> | 150    | 03/08/2002 | OPTIMIZED BLOCKING IMPURITY PLACEMENT FOR SIGE HBTS  | JAGANNATHAN,<br>BASANTH |
| <a href="#"><u>09774126</u></a> | <a href="#"><u>6426265</u></a> | 150    | 01/30/2001 | INCORPORATION OF CARBON IN SILICON/SILICON GERMANIUM EPITAXIAL LAYER TO ENHANCE YIELD FOR SI-GE BIPOLAR TECHNOLOGY                                 | JAGANNATHAN,<br>BASANTH |
| <a href="#"><u>09811859</u></a> | <a href="#"><u>6506656</u></a> | 150    | 03/19/2001 | STEPPED COLLECTOR IMPLANT AND METHOD FOR FABRICATION   | JAGANNATHAN,<br>BASANTH |
| <a href="#"><u>09822587</u></a> | <a href="#"><u>6660607</u></a> | 150    | 03/30/2001 | METHOD FOR FABRICATING HETEROJUNCTION BIPOLAR TRANSISTORS  | JAGANNATHAN,<br>BASANTH |
| <a href="#"><u>09838892</u></a> | <a href="#"><u>6750119</u></a> | 150    | 04/20/2001 | EPITAXIAL AND POLYCRYSTALLINE GROWTH OF Si <sub>1-X</sub> -Ge <sub>X</sub> AND Si <sub>1-Y</sub> Ge <sub>Y</sub> ALLOY LAYERS ON Si BY UHV-CVD     | JAGANNATHAN,<br>BASANTH |
| <a href="#"><u>09843783</u></a> | <a href="#"><u>6780735</u></a> | 150    | 04/30/2001 | METHOD TO INCREASE CARBON AND BORON DOPING CONCENTRATIONS IN Si AND  | JAGANNATHAN,<br>BASANTH |

| SIGE FILMS                  |            |     |            |   |                      |
|-----------------------------|------------|-----|------------|---|----------------------|
| 09885792                    | Not Issued | 161 | 06/20/2001 | Non-self-aligned SiGe heterojunction bipolar transistor   | JAGANNATHAN, BASANTH |
| 09962738                    | 6927476    | 150 | 09/25/2001 | BIPOLAR DEVICE HAVING SHALLOW JUNCTION RAISED EXTRINSIC BASE AND METHOD FOR MAKING THE SAME   | JAGANNATHAN, BASANTH |
| 10047975                    | 6656809    | 150 | 01/15/2002 | METHOD TO FABRICATE SIGE HBTS WITH CONTROLLED CURRENT GAIN AND IMPROVED BREAKDOWN VOLTAGE CHARACTERISTICS   | JAGANNATHAN, BASANTH |
| 10122857                    | 6815802    | 150 | 04/15/2002 | INCORPORATION OF CARBON IN SILICON/SILICON GERMANIUM EPITAXIAL LAYER TO ENHANCE YIELD FOR SI-GE BIPOLAR TECHNOLOGY  | JAGANNATHAN, BASANTH |
| 10249563                    | 6780695    | 150 | 04/18/2003 | BICMOS INTEGRATION SCHEME WITH RAISED EXTRINSIC BASE  | JAGANNATHAN, BASANTH |
| 10316211                    | 6858532    | 150 | 12/10/2002 | LOW DEFECT PRE-EMITTER AND PRE-BASE OXIDE ETCH FOR BIPOLAR TRANSISTORS AND RELATED TOOLING  | JAGANNATHAN, BASANTH |
| 10676171                    | 6787427    | 150 | 10/01/2003 | METHOD TO FABRICATE SIGE HBTS WITH CONTROLLED CURRENT GAIN AND IMPROVED BREAKDOWN VOLTAGE CHARACTERISTICS   | JAGANNATHAN, BASANTH |
| 10711640<br>N.D.P.          | Not Issued | 61  | 09/29/2004 | STRUCTURE AND LAYOUT OF A FET PRIME CELL  | JAGANNATHAN, BASANTH |
| 10753001<br>Q6.             | Not Issued | 161 | 01/07/2004 | Optimized blocking impurity placement for SiGe HBTs   | JAGANNATHAN, BASANTH |
| 10775514                    | Not Issued | 71  | 02/10/2004 | Epitaxial and polycrystalline growth of Si <sub>1-x-y</sub> Ge <sub>x</sub> C <sub>y</sub> and Si <sub>1-y</sub> C <sub>y</sub> alloy layers on Si by UHV-CVD | JAGANNATHAN, BASANTH |
| 10775515<br>N.D.P.<br>(all) | 6908866    | 150 | 02/10/2004 | EPITAXIAL AND POLYCRYSTALLINE GROWTH OF SI <sub>1-X-Y</sub> GE <sub>X</sub> C <sub>Y</sub> AND SI <sub>1-Y</sub> C <sub>Y</sub> ALLOY LAYERS ON SI BY UHV-CVD | JAGANNATHAN, BASANTH |
| 10908448<br>N.D.P.          | Not Issued | 71  | 05/12/2005 | STRUCTURE AND METHOD OF MAKING A FIELD EFFECT TRANSISTOR HAVING AN ASYMMETRICALLY STRESSED  | JAGANNATHAN, BASANTH |

|                                      |            |    |            | CHANNEL REGION   |                      |
|--------------------------------------|------------|----|------------|--|----------------------|
| 10953378<br><i>N, D P<br/>(all.)</i> | Not Issued | 93 | 09/29/2004 | INCORPORATION OF CARBON IN SILICON/SILICON GERMANTUM EPITAXIAL LAYER TO ENHANCE YIELD FOR SI-GE BIPOLAR TECHNOLOGY | JAGANNATHAN, BASANTH |
| 11057176<br><i>N, D P.</i>           | Not Issued | 30 | 02/15/2005 | Single reactor, multi-pressure chemical vapor deposition for semiconductor devices                                 | JAGANNATHAN, BASANTH |

Inventor Search Completed: No Records to Display.

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**PALM INTRANET**
**Inventor Name Search Result**

Your Search was:

Last Name = CHU

First Name = JACK OON

| <b>Application#</b>             | <b>Patent#</b>                 | <b>Status</b> | <b>Date Filed</b> | <b>Title</b>  | <b>Inventor Name</b> |
|---------------------------------|--------------------------------|---------------|-------------------|---|----------------------|
| <a href="#"><u>08840741</u></a> | <a href="#"><u>5780327</u></a> | 150           | 04/16/1997        | VERTICAL DOUBLE-GATE FIELD EFFECT TRANSISTOR                                    | CHU, JACK OON        |
| <a href="#"><u>08846605</u></a> | <a href="#"><u>5906951</u></a> | 150           | 04/30/1997        | STRAINED SI/SIGE LAYERS ON INSULATOR  | CHU, JACK OON        |
| <a href="#"><u>08885611</u></a> | <a href="#"><u>6723621</u></a> | 150           | 06/30/1997        | ABRUPT DELTA-LIKE DOPING IS SI AND SIGE FILMS BY UHV-CVD                        | CHU, JACK OON        |
| <a href="#"><u>09025889</u></a> | <a href="#"><u>6013134</u></a> | 150           | 02/18/1998        | ADVANCE INTEGRATED CHEMICAL VAPOR DEPOSITION (AICVD) FOR SEMICONDUCTOR DEVICES  | CHU, JACK OON        |
| <a href="#"><u>09099978</u></a> | Not Issued                     | 161           | 06/19/1998        | SI/SIGE OPTOELECTRONIC INTEGRATED CIRCUITS                                      | CHU, JACK OON        |
| <a href="#"><u>09107738</u></a> | <a href="#"><u>6096590</u></a> | 150           | 06/30/1998        | SCALABLE MOS FIELD EFFECT TRANSISTOR  | CHU, JACK OON        |
| <a href="#"><u>09267323</u></a> | <a href="#"><u>6350993</u></a> | 150           | 03/12/1999        | HIGH SPEED COMPOSITE P-CHANNEL SI/SIGE HETEROSTRUCTURE FOR FIELD EFFECT DEVICES | CHU, JACK OON        |
| <a href="#"><u>09290778</u></a> | <a href="#"><u>6251751</u></a> | 150           | 04/13/1999        | BULK AND STRAINED SILICON ON INSULATOR USING LOCAL SELECTIVE OXIDATION          | CHU, JACK OON        |
| <a href="#"><u>09311468</u></a> | <a href="#"><u>6059895</u></a> | 150           | 05/13/1999        | STRAINED SI/SIGE LAYERS ON INSULATOR  | CHU, JACK OON        |
| <a href="#"><u>09369995</u></a> | <a href="#"><u>6425951</u></a> | 150           | 08/06/1999        | ADVANCE INTEGRARED CHEMICAL VAPOR DEPOSITION (AICVD) FOR SEMICONDUCTOR          | CHU, JACK OON        |
| <a href="#"><u>09675841</u></a> | <a href="#"><u>6475072</u></a> | 150           | 09/29/2000        | METHOD OF WAFER SMOOTHING FOR BONDING USING CHEMO-MECHANICAL POLISHING (CMP)    | CHU, JACK OON        |
| <a href="#"><u>11065816</u></a> | Not Issued                     | 30            | 02/25/2005        | High performance FET devices and methods thereof                                | CHU, JACK OON        |

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|---------------------------------|------------------|-------------------|---------------|
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|                                 | CHU              | JACK OON          |               |

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**PALM INTRANET**
**Inventor Name Search Result**

Your Search was:

Last Name = GRILL

First Name = ALFRED

| <b>Application#</b>             | <b>Patent#</b>                 | <b>Status</b> | <b>Date Filed</b> | <b>Title</b>  | <b>Inventor Name</b> |
|---------------------------------|--------------------------------|---------------|-------------------|---|----------------------|
| <a href="#"><u>07504496</u></a> | <a href="#"><u>5031029</u></a> | 250           | 04/04/1990        | COPPER DEVICE AND USE THEREOF WITH SEMICONDUCTOR DEVICES                          | GRILL, ALFRED        |
| <a href="#"><u>07634671</u></a> | <a href="#"><u>5159508</u></a> | 150           | 12/27/1990        | MAGNETIC HEAD SLIDER HAVING A PROTECTIVE COATING THEREIN                          | GRILL, ALFRED        |
| <a href="#"><u>07785634</u></a> | <a href="#"><u>5155657</u></a> | 250           | 10/31/1991        | HIGH AREA CAPACITOR FORMATION USING MATERIAL DEPENDENT ETCHING                    | GRILL, ALFRED        |
| <a href="#"><u>07854187</u></a> | Not Issued                     | 166           | 03/20/1992        | METHOD AND APPARATUS FOR FILLING HIGH ASPECT RATIO PATTERNS WITH METAL            | GRILL, ALFRED        |
| <a href="#"><u>07868371</u></a> | <a href="#"><u>5241131</u></a> | 250           | 04/14/1992        | EROSION/CORROSION RESISTANT DIAPHRAGM   | GRILL, ALFRED        |
| <a href="#"><u>07877334</u></a> | <a href="#"><u>5294518</u></a> | 250           | 05/01/1992        | AMORPHOUS WRITE-READ OPTICAL STORAGE MEMORY                                       | GRILL, ALFRED        |
| <a href="#"><u>07951924</u></a> | <a href="#"><u>5302266</u></a> | 250           | 09/25/1992        | METHOD AND APPARATUS FOR FILING HIGH ASPECT PATTERNS WITH METAL                   | GRILL, ALFRED        |
| <a href="#"><u>08144907</u></a> | Not Issued                     | 166           | 10/28/1993        | DIAMOND-LIKE CARBON WRITE-READ OPTICAL STORAGE MEMORY                             | GRILL, ALFRED        |
| <a href="#"><u>08236600</u></a> | Not Issued                     | 161           | 04/29/1994        | ELECTRODE STRUCTURE FOR CAPACITOR WITH HIGH DIELECTRIC CONSTANT MATERIALS         | GRILL, ALFRED        |
| <a href="#"><u>08257396</u></a> | <a href="#"><u>5416042</u></a> | 150           | 06/09/1994        | METHOD OF FABRICATING STORAGE CAPACITORS USING HIGH DIELECTRIC CONSTANT MATERIALS | GRILL, ALFRED        |
| <a href="#"><u>08273689</u></a> | <a href="#"><u>5559367</u></a> | 150           | 07/12/1994        | DIAMOND-LIKE CARBON FOR USE IN VLSI AND ULSI INTERCONNECT SYSTEMS                 | GRILL, ALFRED        |

|                 |         |     |            |   |               |
|-----------------|---------|-----|------------|---|---------------|
| <u>08333405</u> | 5462784 | 150 | 11/02/1994 | FLUORINATED DIAMOND-LIKE CARBON PROTECTIVE COATING FOR MAGNETIC RECORDING MEDIA DEVICES                                 | GRILL, ALFRED |
| <u>08346436</u> | 5461536 | 250 | 11/29/1994 | STORAGE CAPACITORS USING HIGH DIELECTRIC CONSTANT MATERIALS   | GRILL, ALFRED |
| <u>08350249</u> | 5440507 | 150 | 12/06/1994 | DIAMOND-LIKE CARBON WRITE-READ OPTICAL STORAGE MEMORY   | GRILL, ALFRED |
| <u>08371627</u> | 5576579 | 150 | 01/12/1995 | TASIN OXYGEN DIFFUSION BARRIER IN MULTILAYER STRUCTURES   | GRILL, ALFRED |
| <u>08372633</u> | 5625233 | 250 | 01/13/1995 | THIN FILM MULTI-LAYER OXYGEN DIFFUSION BARRIER CONSISTING OF REFRACTORY METAL, REFRACTORY ALUMINIDE, AND ALUMINUM OXIDE | GRILL, ALFRED |
| <u>08465054</u> | 5639316 | 150 | 06/06/1995 | THIN FILM MULTI-LAYER OXYGEN DIFFUSION BARRIER CONSISTING OF ALUMINUM ON REFRACTORY METAL                               | GRILL, ALFRED |
| <u>08474616</u> | 5663854 | 150 | 06/07/1995 | PREBENT CERAMIC SUSPENSION  | GRILL, ALFRED |
| <u>08483682</u> | 5674355 | 250 | 06/07/1995 | DIAMOND-LIKE CARBON FOR USE IN VLSI AND ULSI INTERCONNECT SYSTEMS   | GRILL, ALFRED |
| <u>08537497</u> | 5674638 | 250 | 10/02/1995 | FLUORINATED DIAMOND-LIKE CARBON PROTECTIVE COATING FOR MAGNETIC RECORDING MEDIA DEVICES                                 | GRILL, ALFRED |
| <u>08577165</u> | 5712759 | 150 | 12/22/1995 | SIDEWALL CAPACITOR WITH L-SHAPED DIELECTRIC   | GRILL, ALFRED |
| <u>08577178</u> | 5914851 | 150 | 12/22/1995 | ISOLATED SIDEWALL CAPACITOR   | GRILL, ALFRED |
| <u>08596909</u> | 5869880 | 150 | 03/13/1996 | STRUCTURE AND FABRICATION METHOD FOR STACKABLE, AIR-GAP-CONTAINING LOW EPSILON DIELECTRIC LAYERS                        | GRILL, ALFRED |
| <u>08608893</u> | 5942328 | 150 | 02/29/1996 | LOW DIELECTRIC CONSTANT AMORPHOUS FLUORINATED CARBON AND METHOD OF PREPARATION  | GRILL, ALFRED |
| <u>08631239</u> | 5679269 | 150 | 04/12/1996 | DIAMOND-LIKE CARBON FOR USE IN VLSI AND ULSI  | GRILL, ALFRED |

|                 |            |     |            |  |               |
|-----------------|------------|-----|------------|--|---------------|
|                 |            |     |            | INTERCONNECT SYSTEMS   |               |
| <u>08636456</u> | 5789320    | 150 | 04/23/1996 | PLATING OF NOBLE METAL ELECTRODES FOR DRAM AND FRAM  | GRILL, ALFRED |
| <u>08636624</u> | 5757612    | 150 | 04/23/1996 | STRUCTURE AND FABRICATION METHOD FOR NON-PLANAR MEMORY ELEMENTS  | GRILL, ALFRED |
| <u>08646583</u> | 5776823    | 150 | 05/08/1996 | TASIN OXYGEN DIFFUSION BARRIER IN MULTILAYER STRUCTURES  | GRILL, ALFRED |
| <u>08668241</u> | 5796166    | 150 | 06/21/1996 | TASIN OXYGEN DIFFUSION BARRIER IN MULTILAYER STRUCTURES  | GRILL, ALFRED |
| <u>08798684</u> | 5963397    | 150 | 02/12/1997 | CERAMIC SUSPENSION BENT BY STRESSED PATCH  | GRILL, ALFRED |
| <u>08805403</u> | 6188120    | 150 | 02/24/1997 | METHOD AND MATERIALS FOR THROUGH-MASK ELECTROPLATING AN SELECTIVE BASEREMOVAL                                  | GRILL, ALFRED |
| <u>08866459</u> | 5932907    | 150 | 05/30/1997 | METHOD, MATERIALS, AND STRUCTURES FOR NOBLE METAL ELECTRODE CONTACTS TO SILICON                                | GRILL, ALFRED |
| <u>08866460</u> | Not Issued | 161 | 05/30/1997 | OXIDATION-RESISTANT SILICIDES FOR BARRIER LAYERS   | GRILL, ALFRED |
| <u>08868772</u> | 6428894    | 150 | 06/04/1997 | TUNABLE AND REMOVABLE PLASMA DEPOSITED ANTIREFLECTIVE COATINGS   | GRILL, ALFRED |
| <u>08899099</u> | Not Issued | 161 | 07/24/1997 | STRUCTURE AND FABRICATION METHOD FOR NON-PLANAR MEMORY ELEMENTS  | GRILL, ALFRED |
| <u>08908295</u> | 6131258    | 150 | 08/07/1997 | SIDEWALL CAPACITOR WITH L-SHAPED DIELECTRIC  | GRILL, ALFRED |
| <u>08910179</u> | 6027966    | 150 | 08/13/1997 | ISOLATED SIDEWALL CAPACITOR  | GRILL, ALFRED |
| <u>08916001</u> | 6030904    | 150 | 08/21/1997 | STABILIZATION OF LOW-K CARBON-BASED DIELECTRICS  | GRILL, ALFRED |
| <u>08924476</u> | Not Issued | 161 | 08/25/1997 | LAYERED RESIST SYSTEM USING TUNABLE AMORPHOUS CARBON FILM AS A BOTTOM LAYER AND METHODS OF FABRICATION THEREOF | GRILL, ALFRED |
| <u>08972993</u> | 5945155    | 150 | 11/19/1997 | LOW DIELECTRIC CONSTANT AMORPHOUS FLUORINATED  | GRILL, ALFRED |

| CARBON AND METHOD OF PREPARATION |                                |     |            |   |               |
|----------------------------------|--------------------------------|-----|------------|---|---------------|
| <a href="#"><u>08974081</u></a>  | <a href="#"><u>5942769</u></a> | 150 | 11/19/1997 | LOW DIELECTRIC CONSTANT AMORPHOUS FLUORINATED CARBON AND METHOD OF PREPARATION  | GRILL, ALFRED |
| <a href="#"><u>09058651</u></a>  | <a href="#"><u>5981000</u></a> | 150 | 04/10/1998 | METHOD FOR FABRICATING A THERMALLY STABLE DIAMOND-LIKE CARBON FILM  | GRILL, ALFRED |
| <a href="#"><u>09067439</u></a>  | <a href="#"><u>6448655</u></a> | 150 | 04/28/1998 | STABILIZATION OF FLUORINE-CONTAINING LOW-K DIELECTRICS IN A METAL/INSULATOR WIRING STRUCTURE BY ULTRAVIOLET IRRADIATION                         | GRILL, ALFRED |
| <a href="#"><u>09107567</u></a>  | <a href="#"><u>6147009</u></a> | 150 | 06/29/1998 | HYDROGENATED OXIDIZED SILICON CARBON MATERIAL   | GRILL, ALFRED |
| <a href="#"><u>09126212</u></a>  | <a href="#"><u>6140226</u></a> | 150 | 07/30/1998 | DUAL DAMASCENE PROCESSING FO SEMICONDUCTOR CHIP INTERCONNECTS   | GRILL, ALFRED |
| <a href="#"><u>09132608</u></a>  | <a href="#"><u>6265779</u></a> | 150 | 08/11/1998 | METHOD AND MATERIAL FOR INTEGRATION OF FUORINE-CONTAINING LOW-K DIELECTRICS   | GRILL, ALFRED |
| <a href="#"><u>09139367</u></a>  | Not Issued                     | 161 | 08/25/1998 | LITHOGRAPHIC STRUCTURES HAVING INDEX OF REFRACTION AND EXTINCTION COFFICIENTS PROFILES FOR CONTROLLING REFLECTION TO CONTROL UNEWIDTH VARIATION | GRILL, ALFRED |
| <a href="#"><u>09192133</u></a>  | <a href="#"><u>6017814</u></a> | 150 | 11/13/1998 | STRUCTURE AND FABRICATION METHOD FOR STACKABLE, AIR-GAP-CONTAINING LOW EPSILON DIELECTRIC LAYERS  | GRILL, ALFRED |
| <a href="#"><u>09281208</u></a>  | <a href="#"><u>6049443</u></a> | 150 | 03/30/1999 | SUSPENSION BENT BY STRESSED PATCH   | GRILL, ALFRED |
| <a href="#"><u>09303595</u></a>  | <a href="#"><u>6242321</u></a> | 150 | 05/03/1999 | STRUCTURE AND FABRICATION METHOD FOR NON-PLANAR MEMORY ELEMENTS   | GRILL, ALFRED |

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**PALM INTRANET****Inventor Name Search Result**

Your Search was:

Last Name = OTT

First Name = JOHN ALBRECHT

| Application# | Patent# | Status | Date Filed | Title  | Inventor Name      |
|--------------|---------|--------|------------|--|--------------------|
| 08951827     | 5963817 | 150    | 10/16/1997 | BULK AND STRAINED SILICON ON INSULATOR USING LOCAL SELECTIVE OXIDATION | OTT, JOHN ALBRECHT |
| 09290778     | 6251751 | 150    | 04/13/1999 | BULK AND STRAINED SILICON ON INSULATOR USING LOCAL SELECTIVE OXIDATION | OTT, JOHN ALBRECHT |

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**PALM INTRANET**
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Last Name = MEYERSON

First Name = BERNARD

| <b>Application#</b>             | <b>Patent#</b>                 | <b>Status</b> | <b>Date Filed</b> | <b>Title</b>   | <b>Inventor Name</b>    |
|---------------------------------|--------------------------------|---------------|-------------------|--|-------------------------|
| <a href="#"><u>06394018</u></a> | <a href="#"><u>4436797</u></a> | 150           | 06/30/1982        | X-RAY MASK   | MEYERSON,<br>BERNARD S. |
| <a href="#"><u>06481538</u></a> | <a href="#"><u>4526593</u></a> | 150           | 04/04/1983        | RESTRICTOR PLUG DEVICE WITH FILTER FOR A GAS SUPPLY SYSTEM   | MEYERSON,<br>BERNARD S. |
| <a href="#"><u>06559583</u></a> | <a href="#"><u>4504331</u></a> | 150           | 12/08/1983        | SILICON DOPANT SURCE IN INTERMETALLIC SEMICONDUCTOR GROWTH OPERATIONS  | MEYERSON,<br>BERNARD S. |
| <a href="#"><u>06567303</u></a> | Not Issued                     | 166           | 12/30/1983        | METHOD FOR PRODUCING HIGH ENERGY ELECTROLUMINESCENT DEVICES  | MEYERSON,<br>BERNARD S. |
| <a href="#"><u>06626504</u></a> | <a href="#"><u>4592933</u></a> | 150           | 06/29/1984        | HIGH EFFICIENCY HOMOGENEOUS CHEMICAL VAPOR DEPOSITION  | MEYERSON,<br>BERNARD S. |
| <a href="#"><u>06793517</u></a> | <a href="#"><u>4647494</u></a> | 150           | 10/31/1985        | SILICON/CARBON PROTECTION OF METALLIC MAGNETIC STRUCTURES  | MEYERSON,<br>BERNARD S. |
| <a href="#"><u>06895119</u></a> | <a href="#"><u>4684542</u></a> | 150           | 08/11/1986        | LOW PRESSURE CHEMICAL VAPOR DEPOSITION OF TUNGSTEN SILICIDE  | MEYERSON,<br>BERNARD S. |
| <a href="#"><u>06906854</u></a> | Not Issued                     | 166           | 09/12/1986        | METHOD AND APPARATUS FOR LOW TEMPERATURE, LOW PRESSURE CHEMICAL VAPOR DEPOSITION OF EPITAXIAL SILICON LAYERS | MEYERSON,<br>BERNARD S. |
| <a href="#"><u>06921985</u></a> | Not Issued                     | 166           | 10/22/1986        | METHOD FOR PRODUCING HIGH ENERGY ELECTROLUMINESCENT DEVICES  | MEYERSON,<br>BERNARD S. |
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